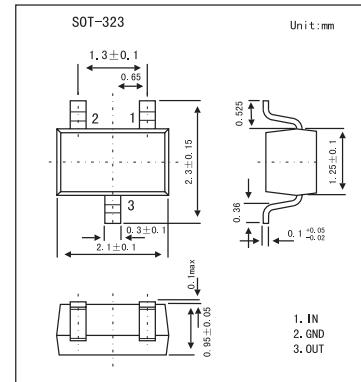


## Schottky barrier (double) diodes

**1PS70SB10; 1PS70SB14  
1PS70SB15; 1PS70SB16**

### ■ Features

- Low forward voltage
- Guard ring protected
- Very small plastic SMD package



### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Conditions	Min	Max	Unit
Continuous reverse voltage	V <sub>R</sub>			30	V
Continuous forward current	I <sub>F</sub>			200	mA
Repetitive peak forward current	I <sub>FRM</sub>	t <sub>p</sub> ≤ 1s, δ ≤ 0.5		300	mA
Non-repetitive peak forward current	I <sub>FSM</sub>	t <sub>p</sub> < 10 ms		600	mA
Total power dissipation (per package)	P <sub>tot</sub>	T <sub>a mb</sub> < 25 °C		200	mW
Storage temperature	T <sub>stg</sub>		-65	+150	°C
Junction temperature	T <sub>j</sub>			125	°C
Operating ambient temperature	T <sub>a mb</sub>		-65	+125	°C
thermal resistance from junction to ambient	R <sub>th j-a</sub>			625	K/W

### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Max	Unit
Continuous forward voltage	V <sub>F</sub>	I <sub>F</sub> = 0.1 mA		240	mV
		I <sub>F</sub> = 1 mA		320	mV
		I <sub>F</sub> = 10 mA		400	mV
		I <sub>F</sub> = 30 mA		500	mV
		I <sub>F</sub> = 100 mA		800	mV
Reverse current	I <sub>R</sub>	V <sub>R</sub> = 25 V, Note 1	2	15	µ A
Diode capacitance	C <sub>d</sub>	V <sub>R</sub> = 0 V; f = 1 MHz	10	50	pF

Note

1. Pulse test: t<sub>p</sub> < 300 µ s; δ ≤ 0.02.

### ■ Marking

Type	1PS70SB10	1PS70SB14	1PS70SB15	1PS70SB16
Marking	7*0	7*4	7*5	7*6